

# MCC

Micro Commercial Components  
21201 Itasca Street Chatsworth  
CA 91311  
Phone: (818) 701-4933  
Fax: (818) 701-4939

## 1N914(A)(B)

### Features

- Low Current Leakage
- Compression Bond Construction
- Low Cost

### 500mW 100 Volt Silicon Epitaxial Diodes

### Maximum Ratings

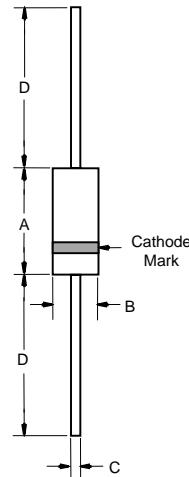
- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Maximum Thermal Resistance; 300°C/W Junction To Ambient

Electrical Characteristics @ 25°C Unless Otherwise Specified

Maximum Repetitive Reverse Voltage	$V_{RRM}$	100V	
Average Rectified Forward Current	$I_o$	200mA	
Power Dissipation	$P_D$	500mW	
Junction Temperature	$T_J$	150°C	
Peak Forward Surge Current	$I_{FSM}$	1.0A 4.0A	Pulse Width=1.0 second Pulse Width=1.0 microsecond
Minimum Breakdown Voltage	$V_R$	100V 75V	$I_R=100\mu A$ , $I_R=5.0\mu A$
Maximum Instantaneous Forward Voltage 1N914 1N914 A 1N914 B 1N914 B	$V_F$	1.0V 720mV	$T_J = 25^\circ C$ $I_{FM} = 10mA$ ; $I_{FM} = 20mA$ ; $I_{FM} = 100mA$ ; $I_{FM} = 5.0mA$ ;
Maximum Reverse Current	$I_R$	25nA 5.0uA 50uA	$V_R=20V$ , $T_J=25^\circ C$ , $V_R=75V$ , $T_J=25^\circ C$ , $V_R=20V$ , $T_J=150^\circ C$
Typical Junction Capacitance	$C_J$	4.0pF	Measured at 1.0MHz, $V_R=0V$
Reverse Recovery Time	$T_{rr}$	4.0nS	$I_F=10mA$ $V_R = 6V$ $R_L=100 \Omega$ , $I_{rr}=1.0mA$

\*Pulse test: Pulse width 300 usec, Duty cycle 2%

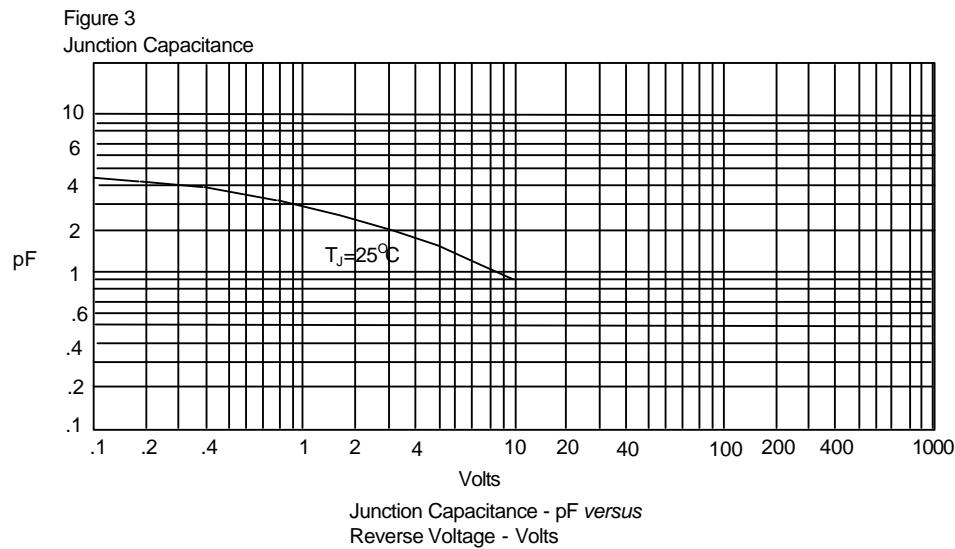
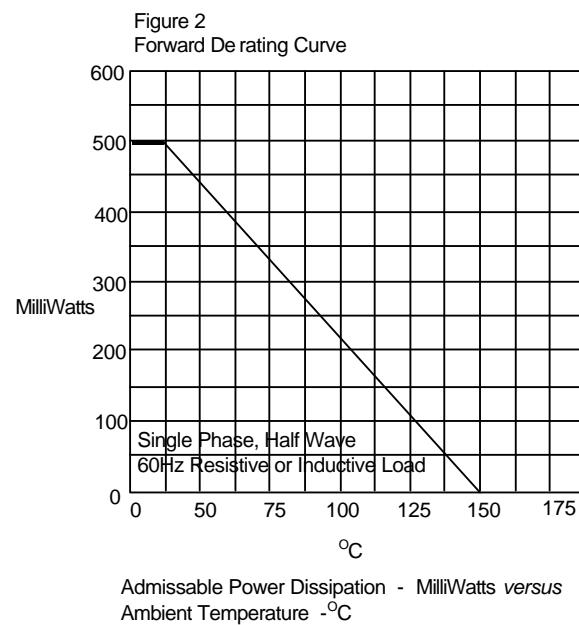
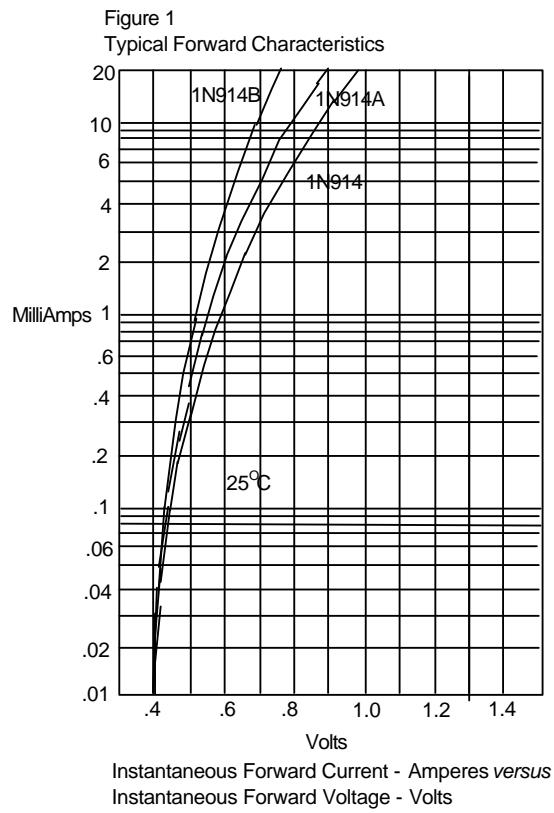
### DO-35



DIM	DIMENSIONS			
	INCHES		MM	
	MIN	MAX	MIN	MAX
A	---	.166	---	.42
B	---	.079	---	2.00
C	---	.020	---	.52
D	1.000	---	25.40	---

[www.mccsemi.com](http://www.mccsemi.com)

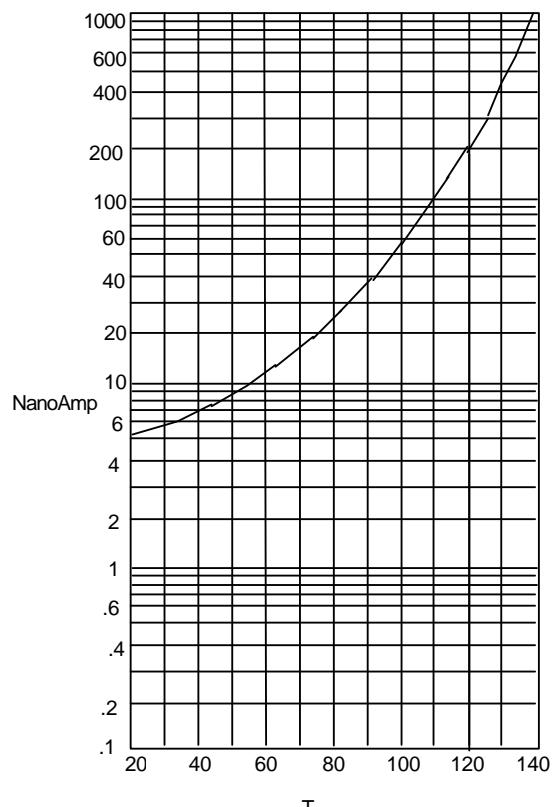
# 1N914(A)(B)



**MCC**

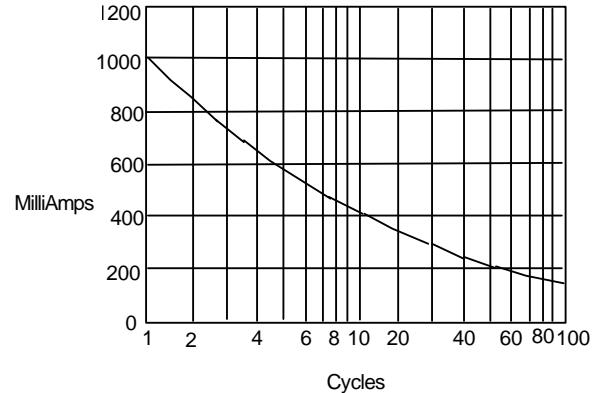
## 1N914(A)(B)

Figure 4  
Typical Reverse Characteristics



Instantaneous Reverse Leakage Current - NanoAmperes  
versus Junction Temperature -  $^{\circ}\text{C}$

Figure 5  
Peak Forward Surge Current



Peak Forward Surge Current - Amperes versus  
Number Of Cycles At 60Hz - Cycles